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Microwave rectification characteristics of Gated-Anode AlGaN/GaN-HEMT-Based Diode

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This presentation will discuss a gated-anode AlGaN/GaN-HEMT-based diode and its rectification characteristics. One of futures of the gated-anode diode is low turn-on voltage and high current with high breakdown voltage. Thanks to the future, we confirm in a circuit simulation with a diode non-linear device model that the diode can be achieved high conversion efficiency of over 80% under over-Watt 5.8-GHz input conditions.